

REMARKS

The patent to Yu talks about dose, not concentration. Therefore, it is uninforming as to concentration. Moreover, it is silent on whether or not strained source/drain regions are formed. Without knowing what Yu actually did, there is no way to determine that Yu formed strained source/drain regions. Since strained source/drain regions need not necessarily form, there can be no finding of inherency.

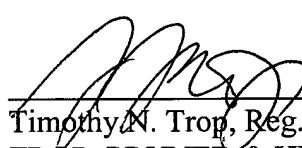
The patent to Brown does not make P-type source/drain regions. See column 3, lines 47-50.

The patent to Liu simply uses a germanium implant to make amorphous (damaged) silicon. Then, the amorphous region is melted. There is simply no way for the Examiner to conclude that, under such unusual circumstances, a strained junction might or might not result. Since it cannot be presumed that a strained source/drain junction occurs there is no basis for a rejection based on Liu. Liu cannot inherently form a strained source/drain junction since there is no way to know what the effect of amorphization, melting, or other variables on the process have on whether or not a strained source/drain junction ends up being formed. Liu never suggests that a strained source/drain junction is formed.

Moreover, Liu only talks about dose, which does not tell you anything about concentration. Dose is simply the rate at which the species are implanted. Concentration is a function of dose and time. Without knowing time, one cannot deduce concentration from dose.

In view of these remarks, the application should now be in condition for allowance.

Respectfully submitted,



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